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| [Home](https://xitanghkust.github.io/index.htm)  [Projects](https://xitanghkust.github.io/projects.htm)  [Publications](https://xitanghkust.github.io/publications.htm)  [Teaching](https://xitanghkust.github.io/teaching.htm)  [Contact](https://xitanghkust.github.io/contact.htm) | |  |  | | --- | --- | |  | Patents | |  | [1] Kevin J. Chen, Baikui Li, **Xi Tang**; P-Doping-Free Schottky-on-Heterojunction Light-Emitting Diode and High-Electron-Mobility Light-Emitting Transistor (International Publication Number: WO 2015/131846 A1)  [2] Kevin J. Chen, Baikui Li, **Xi Tang**; Transistors having On-chip Integrated Photon Source or Photonic-Ohmic Drain to Facilitate De-Trapping Electrons Trapped in Deep Traps of Transistors (US 10,270,436) | |  | Journal articles | |  | **(*first author# or corresponding author\**):** | |  | [1] **X. Tang#**, R. Qiu, Y. Liu, and B. Li. 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